VCRR40P40K

VCRR P-ChannelEnhancement Mode Power MOSFET

Description

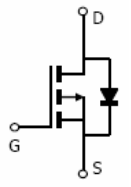
The VCRR40P40K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

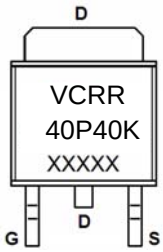
- V_{DS} =-40V,I_D =-40A
  $R_{DS(ON)}$ <14mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ <24mΩ @ V_{GS}=-4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

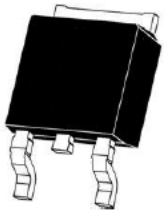
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package
VCRR40P40K		TO-252-2L

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-40	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	-28	A
Pulsed Drain Current	I_{DM}	-160	A
Maximum Power Dissipation （T_C=25°C）	P_D （T_C=25°C）	80	W
Maximum Power Dissipation (T_A=25℃)	P_D (T_A=25℃)	2.5	W
Derating factor		0.53	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	544	mJ
Drain Source voltage slope, V_{DS} ≤-32 V,	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} ≤-32 V, I_{SD}<I_D	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case(Note 2)	$R_{\theta JC}$	1.88	℃/W
Thermal Resistance,Junction-to-Ambient(Note 2)	$R_{\theta JA}$	50	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

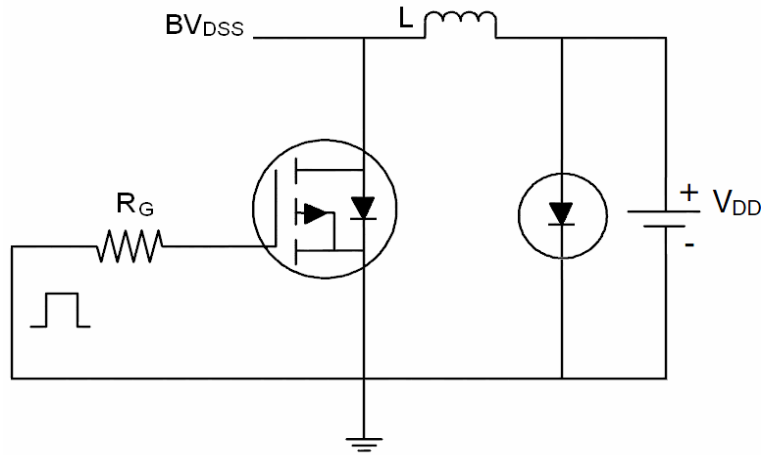
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.5	-1.9	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-12A	-	12	14	mΩ
		V_{GS}=-4.5V, I_D=-12A	-	18.5	24	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-12A	-	34	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-20V,V_{GS}=0V, F=1.0MHz	-	2960	-	PF
Output Capacitance	C_{oss}		-	370	-	PF
Reverse Transfer Capacitance	C_{rss}		-	310	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-20V,I_D=-12A V_{GS}=-10V,R_G=3Ω	-	10	-	nS
Turn-on Rise Time	t_r		-	18	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	t_f		-	24	-	nS
Total Gate Charge	Q_g	V_{DS}=-20,I_D=-12A, V_{GS}=-10V	-	42.2	72	nC
Gate-Source Charge	Q_{gs}		-	6.9		nC
Gate-Drain Charge	Q_{gd}		-	9.7		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-12A	-		-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-40	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F =- 12A di/dt = -100A/μs (Note3)	-	40		nS
Reverse Recovery Charge	Qrr		-	42		nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

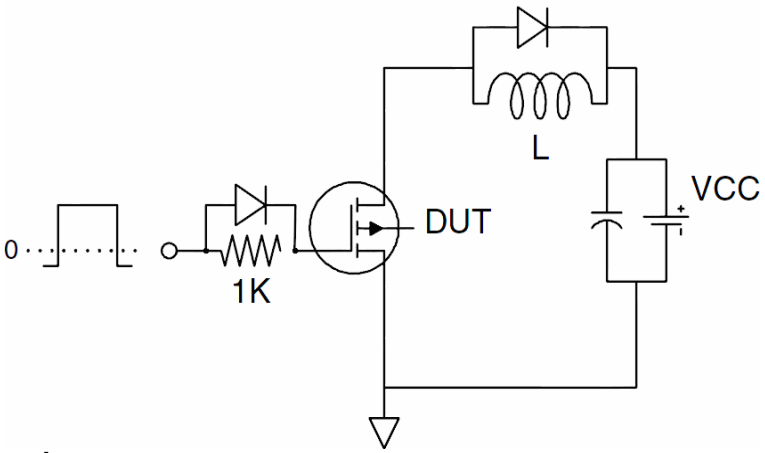
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board with 2oz. Copper, in a still air environment with T_A=25°C., t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: Tj=25℃,V_{DD}=-20V,V_G=-10V,L=1mH,Rg=25Ω

Test Circuit

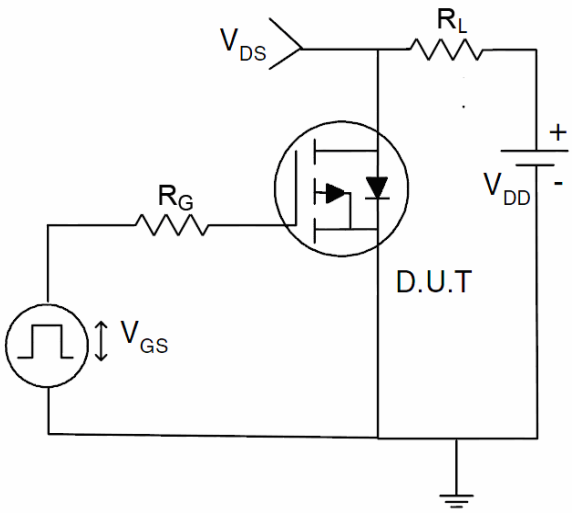
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

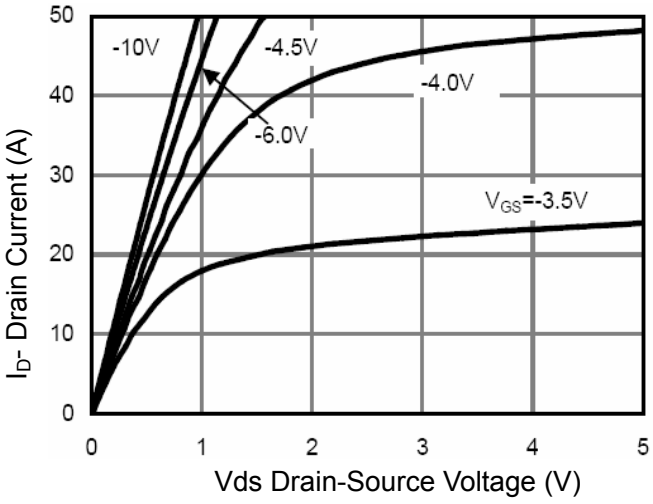


Figure 1 Output Characteristics

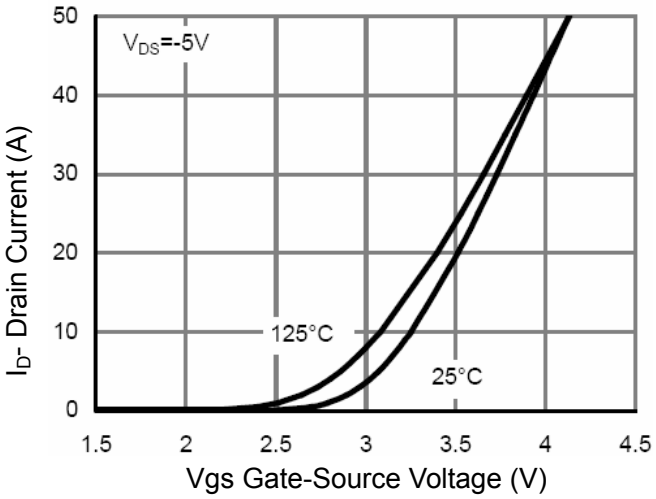


Figure 2 Transfer Characteristics

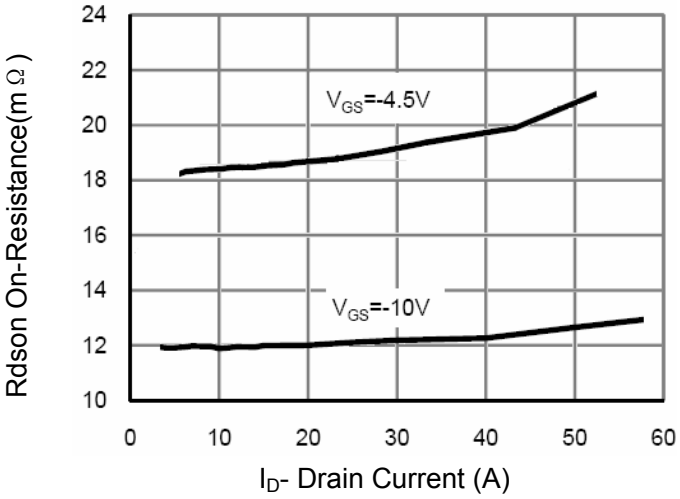


Figure 3 Rdson- Drain Current

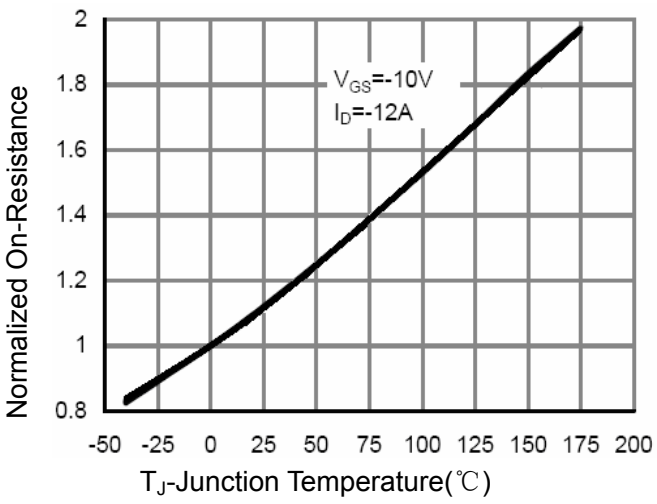


Figure 4 Rdson-Junction Temperature

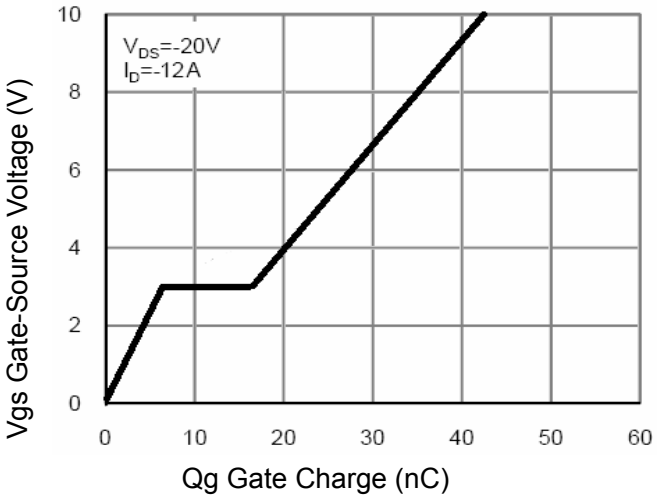


Figure 5 Gate Charge

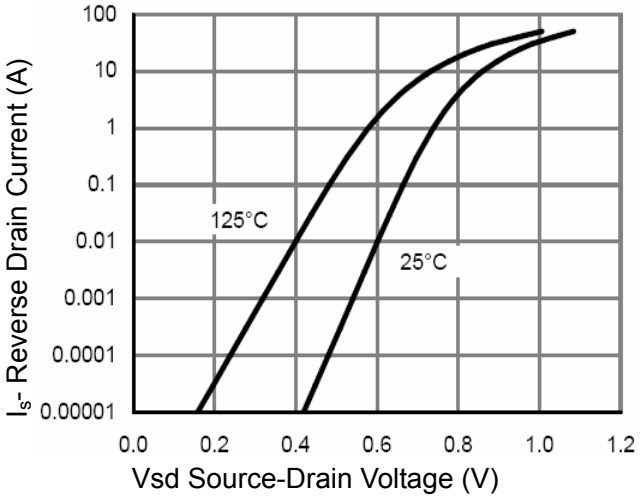


Figure 6 Source- Drain Diode Forward

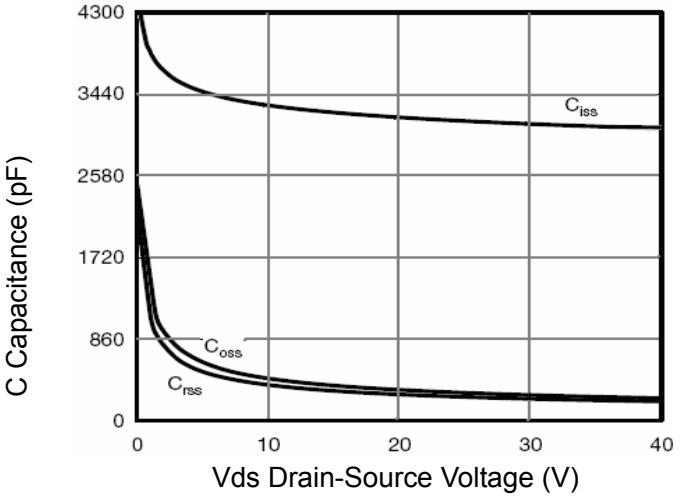


Figure 7 Capacitance vs Vds

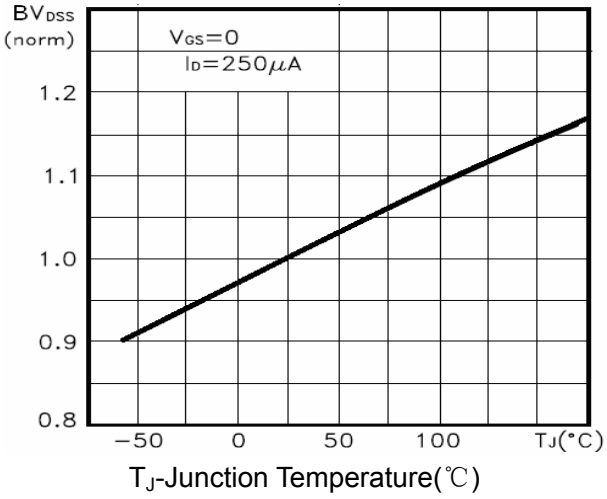


Figure 9 BV_{DSS} vs Junction Temperature

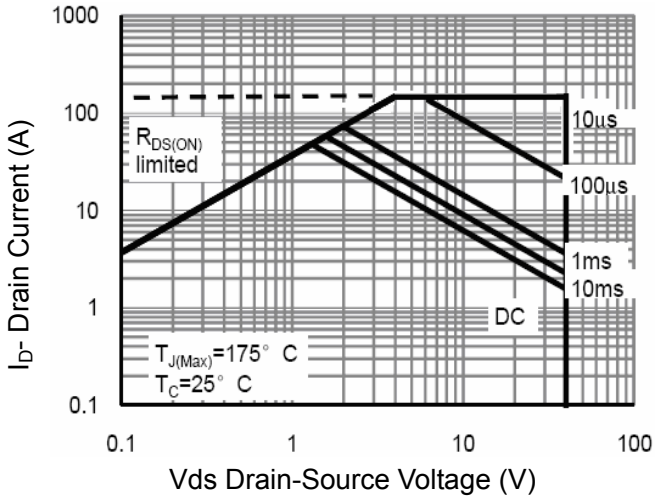


Figure 8 Safe Operation Area

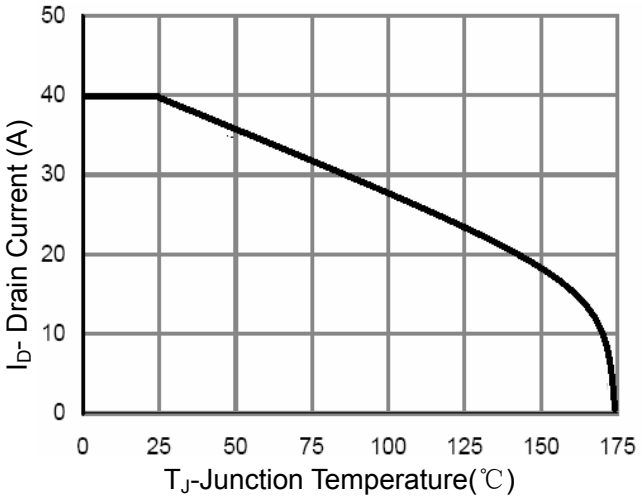


Figure 10 ID Current Derating vs Junction Temperature

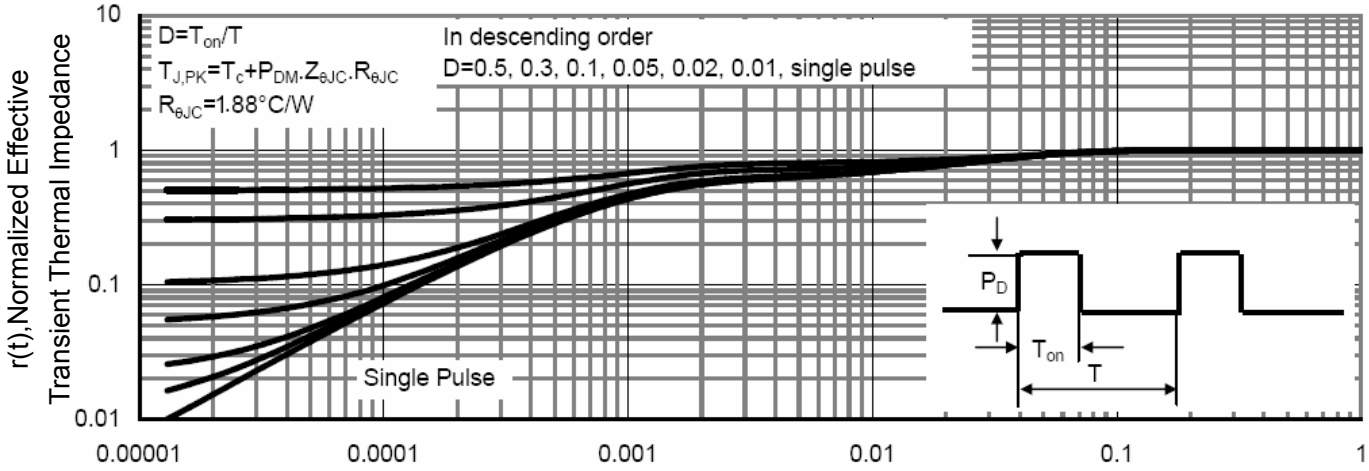


Figure 11 Normalized Maximum Transient Thermal Impedance

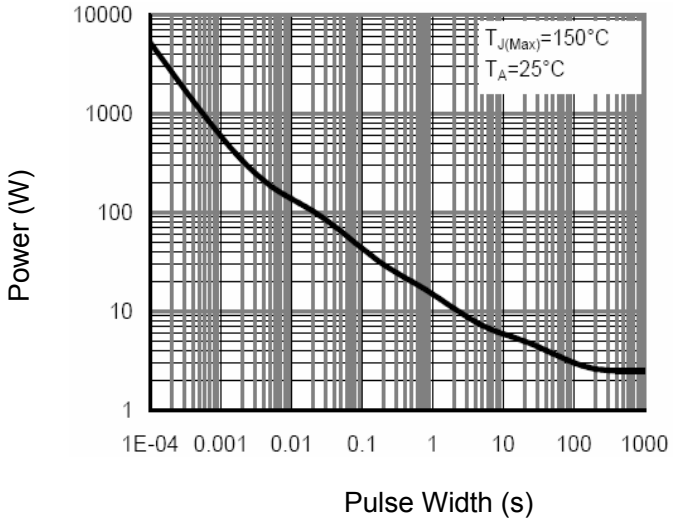
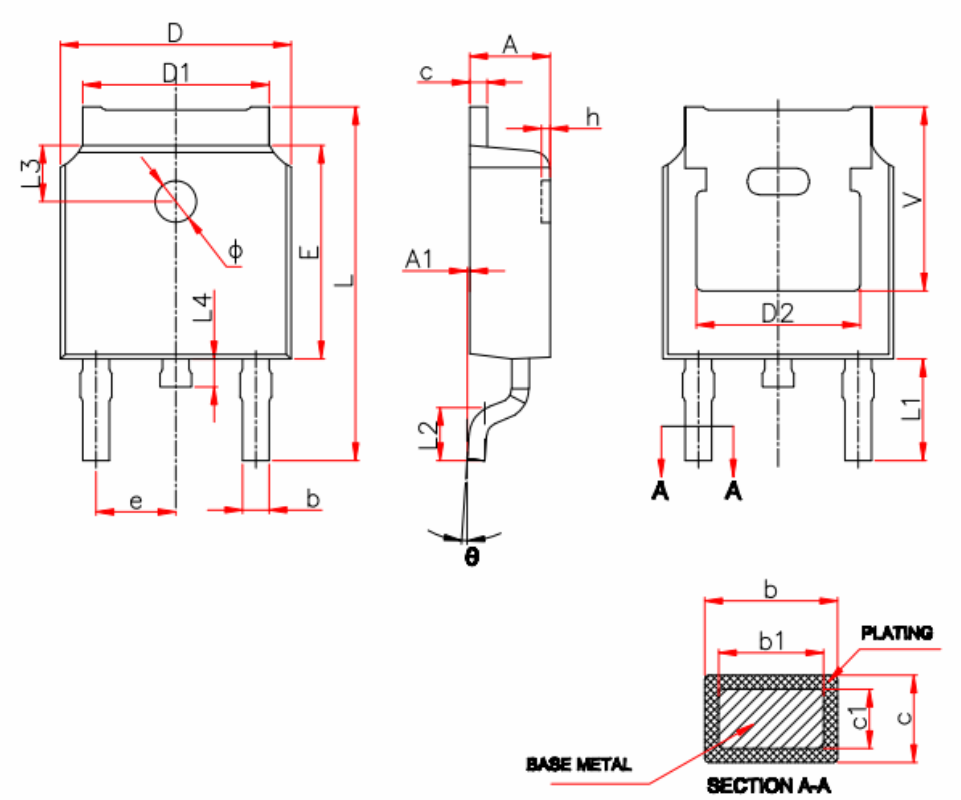


Figure 12 Single Pulse Power Rating Junction-to-Ambient

TO-252 Package Information



Symbol	Millimeters	
	Min.	Max.
A	2.20	2.40
A1	0.00	0.13
b	0.66	0.86
b1	0.73	0.79
c	0.46	0.58
c1	0.50	0.52
D	6.50	6.70
D1	5.10	5.46
D2	4.83 REF.	
E	6.00	6.20
e	2.19	2.39
L	9.80	10.40
L1	2.90 REF.	
L2	1.40	1.70
L3	1.60 REF.	
L4	0.60	1.00
Φ	1.10	1.30
θ	0°	8°

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